

### **Silicon NPN Power Transistor**

#### **DESCRIPTION**

- High Voltage: V<sub>CEV</sub>= 400V(Min)
- Low Saturation Voltage-
  - : V<sub>CE(sat)</sub>= 1.0V(Max.)@ I<sub>C</sub>= 5A

#### **APPLICATIONS**

 Designed for use in horizontal deflection output stages of TV's and CRT's

#### ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

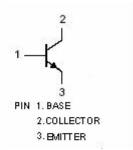
SYMBOL	PARAMETER	VALUE	UNIT	
V <sub>CBO</sub>	Collector-Base Voltage	400	V	
V <sub>CEO</sub>	Collector-Emitter Voltage	200	V	
V <sub>EBO</sub>	Emitter-Base Voltage	6	V	
Ic	Collector Current-Continuous	7	А	
I <sub>CP</sub>	Collector Current-Peak Repetitive	10	Α	
I <sub>CP</sub>	Collector Current- Peak (10ms)	15	А	
I <sub>B</sub>	Base Current	4	Α	
Pc	Collector Power Dissipation @ Tc=25℃	65	W	
TJ	Junction Temperature	150	$^{\circ}$	
T <sub>stg</sub>	Storage Temperature Range	-55~150	$^{\circ}$	

#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT	
Rth j-c	Thermal Resistance, Junction to Case	2.08	°C/W	
R <sub>th j-a</sub>	Thermal Resistance, Junction to Ambient	70	°C/W	

# **Ordering Information**

Product	Package	Packaging
BU406DT9TL	TO-252	Tube





Package Type TO-252



#### **ELECTRICAL CHARACTERISTICS**

#### $T_{\text{C}}$ =25°C unless otherwise specified

10-20 © unicos outerwise specimen							
SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT	
V <sub>CEO(SUS)</sub>	Collector-Emitter Sustaining Voltage	I <sub>C</sub> = 50mA ;I <sub>B</sub> = 0	150			V	
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 5A; I <sub>B</sub> = 0.8A			1.0	V	
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 5A; I <sub>B</sub> = 0.5A			1.2	V	
Ices	Collector Cutoff Current	V <sub>CE</sub> = 400V; V <sub>BE</sub> = 0 V <sub>CE</sub> =250V; V <sub>BE</sub> = 0			5.0 0.1	mA	
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 6V; I <sub>C</sub> = 0			1.0	mA	
h <sub>FE</sub>	DC Current Gain	I <sub>C</sub> = 2A; V <sub>CE</sub> = 5V	60	70	80		
f <sub>T</sub>	Current-Gain—Bandwidth Product	I <sub>C</sub> = 0.5A; V <sub>CE</sub> = 10V	10	30		MHz	
t <sub>f</sub>	Fall Time	I <sub>C</sub> = 5A; I <sub>B1</sub> = -I <sub>B2</sub> = 0.8A			0.4	μs	

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